

150V N-Channel Enhancement Mode Power MOSFET

Description

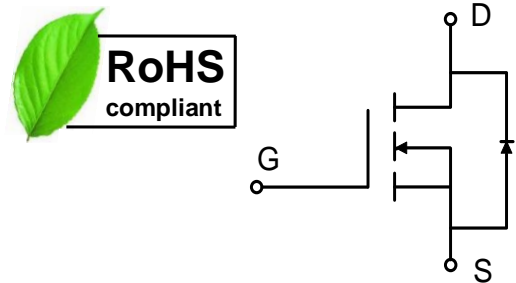
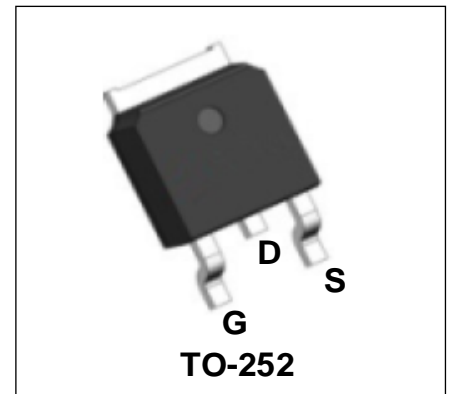
WMO15N15T1 uses advanced power trench technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Features

- $V_{DS} = 150V$, $I_D = 15A$
 $R_{DS(on)} < 170m\Omega$ @ $V_{GS} = 10V$
- High Density Cell Design for Ultra Low $R_{DS(on)}$
- Fully Characterized Avalanche Voltage and Current
- Excellent Package for Good Heat Dissipation

Applications

- Power Switching Application
- Hard Switched and High Frequency Circuits



Absolute Maximum Ratings

| Parameter | | Symbol | Value | Unit |
|--|--------------------|----------------|------------|------------|
| Drain-Source Voltage | | V_{DS} | 150 | V |
| Gate-Source Voltage | | V_{GS} | ± 20 | V |
| Continuous Drain Current ¹ | $T_C = 25^\circ C$ | I_D | 15 | A |
| Pulsed Drain Current ² | | I_{DM} | 50 | A |
| Single Pulse Avalanche Energy ³ | | E_{AS} | 8 | mJ |
| Avalanche Current | | I_{AS} | 4 | A |
| Total Power Dissipation ⁴ | $T_C = 25^\circ C$ | P_D | 44.6 | W |
| Operating Junction and Storage Temperature Range | | T_J, T_{STG} | -55 to 150 | $^\circ C$ |

Thermal Characteristics

| Parameter | Symbol | Value | Unit |
|--|-----------------|-------|--------------|
| Thermal Resistance from Junction-to-Caset ¹ | $R_{\theta JC}$ | 2.8 | $^\circ C/W$ |

Electrical Characteristics

$T_c = 25^\circ\text{C}$, unless otherwise noted

| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
|--|----------------------|---|------|------|------|------|
| Static Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} = 0V, I _D = 250μA | 150 | - | - | V |
| Gate-body Leakage current | I _{GSS} | V _{DS} = 0V, V _{GS} = ±20V | - | - | ±100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 150V, V _{GS} = 0V | - | - | 1 | μA |
| Gate-Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250μA | 1.5 | 2.0 | 2.5 | V |
| Drain-Source On-Resistance ² | R _{DS(on)} | V _{GS} = 10V, I _D = 6A | - | 130 | 170 | mΩ |
| Dynamic Characteristics | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 25V, V _{GS} =0V, f =1MHz | - | 1130 | - | pF |
| Output Capacitance | C _{oss} | | - | 53 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 37 | - | |
| Switching Characteristics | | | | | | |
| Gate Resistance | R _g | V _{DS} =0V, V _{GS} =0V, f =1MHz | - | 1.0 | - | Ω |
| Total Gate Charge | Q _g | V _{GS} = 10V, V _{DS} = 75V, I _D = 1.5A | - | 16 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 4.7 | - | |
| Gate-Drain Charge | Q _{gd} | | - | 5.8 | - | |
| Turn-On Delay Time | t _{d(on)} | V _{GS} =10V, V _{DS} = 75V R _G = 6Ω, I _D = 1A, R _L = 75Ω | - | 6 | - | nS |
| Rise Time | t _r | | - | 8 | - | |
| Turn-Off Delay Time | t _{d(off)} | | - | 17 | - | |
| Fall Time | t _f | | - | 12.5 | - | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Diode Forward Voltage ² | V _{SD} | I _S = 1A, V _{GS} = 0V | - | - | 1.2 | V |
| Continuous Source Current ^{1,5} | I _S | V _G =V _D =0V, Force Current | - | - | 15 | A |

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating. The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 1mH, I_{AS} = 4A$
4. The power dissipation is limited by 150°C junction temperature
5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

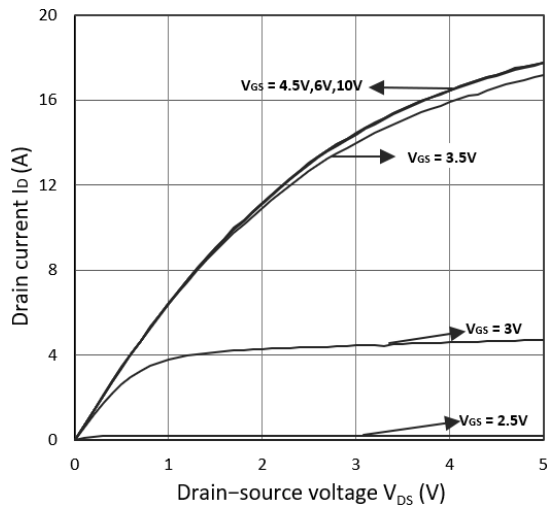


Figure 1. Typical Output Characteristics

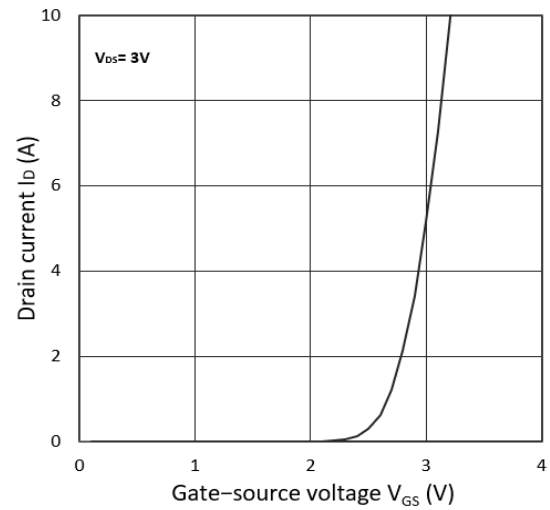


Figure 2. Transfer Characteristics

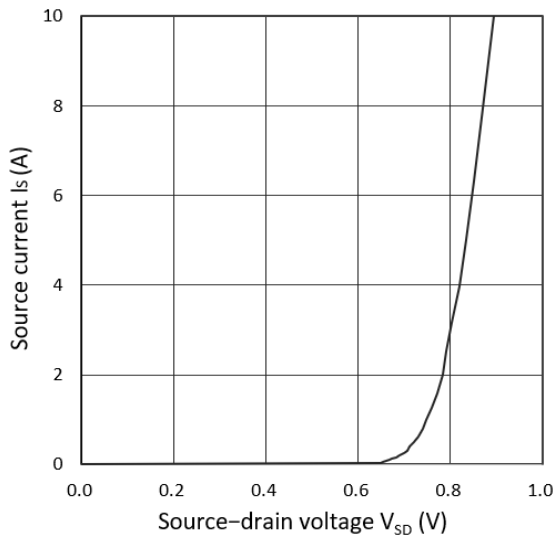


Figure 3. Forward Characteristics of Reverse

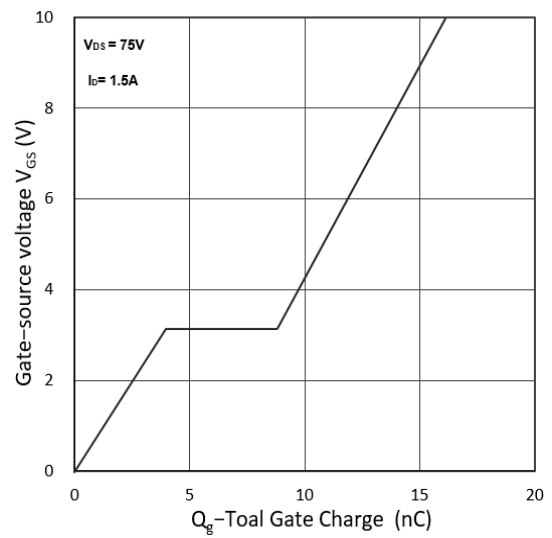
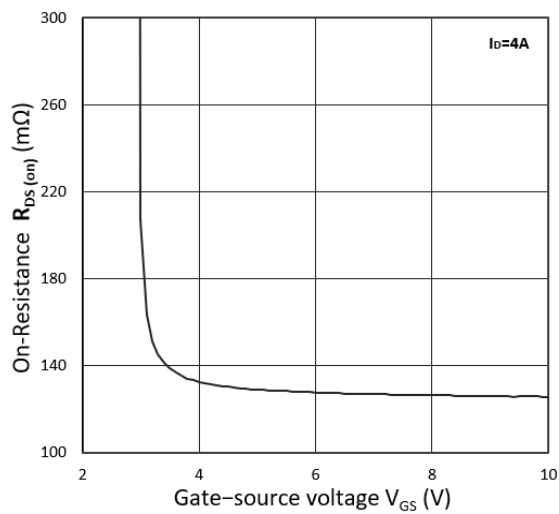
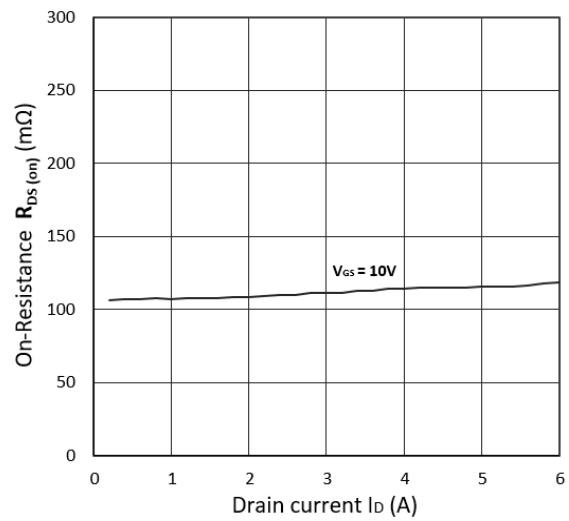


Figure 4. Gate Charge Characteristics

Figure 5. $R_{DS(on)}$ vs. V_{GS} Figure 6. $R_{DS(on)}$ vs. I_D

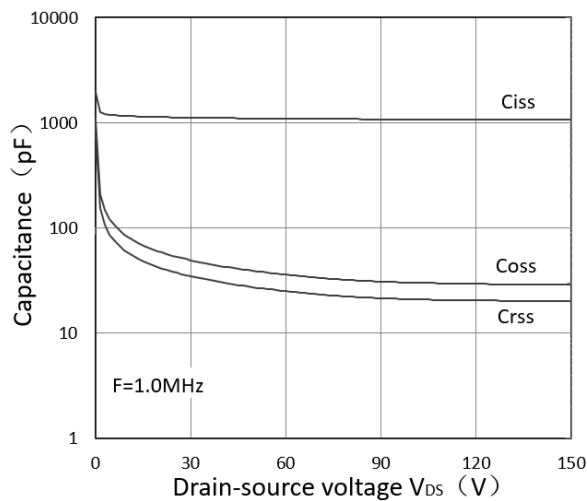


Figure 7. Capacitance Characteristics

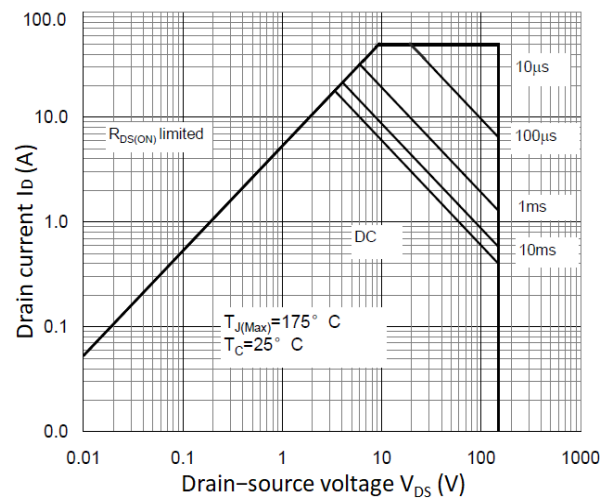


Figure 8. Safe Operating Area

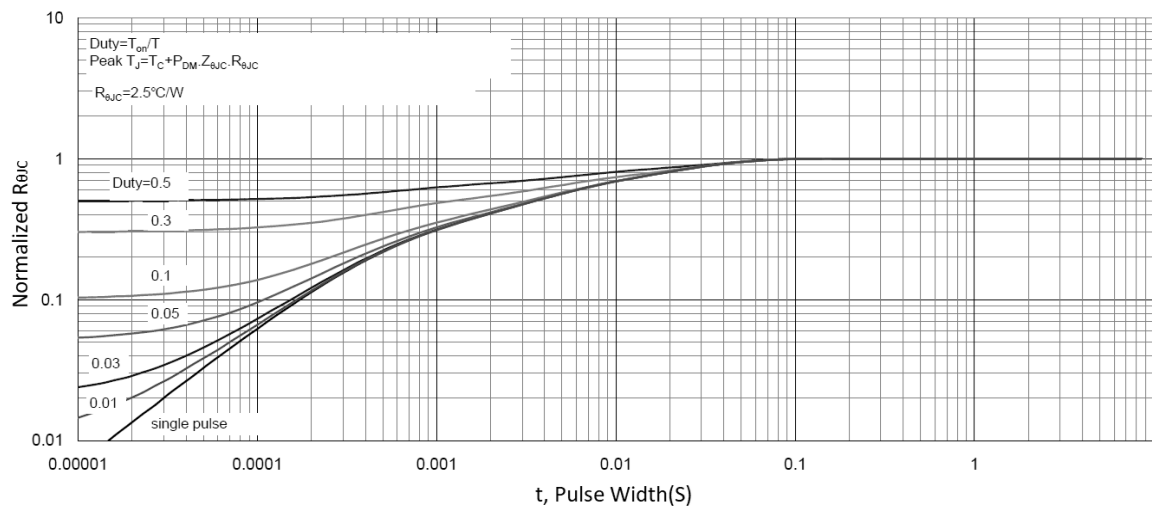


Figure 9. Normalized Maximum Transient Thermal Impedance

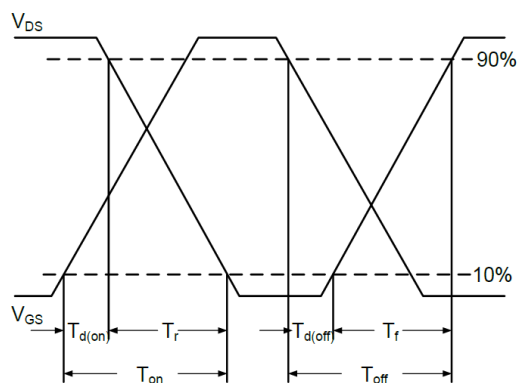
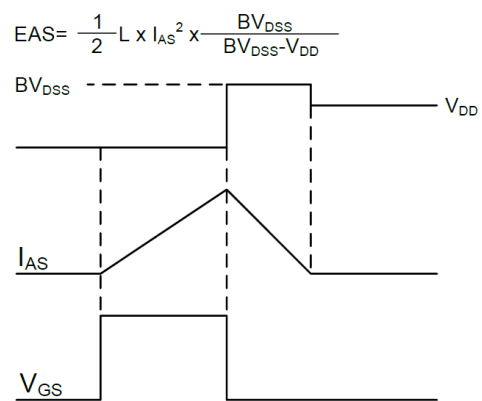
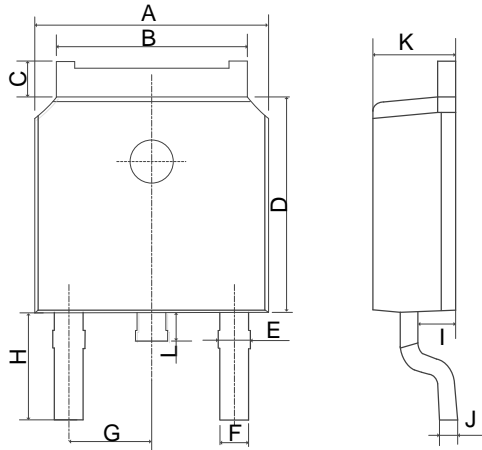


Figure 10. Switching Time Waveform

Figure 11. Unclamped Inductive Switching
Waveform

Mechanical Dimensions for TO-252

COMMON DIMENSIONS

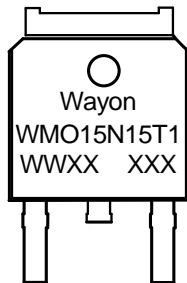


| SYMBOL | MM | |
|--------|---------|------|
| | MIN | MAX |
| A | 6.40 | 6.80 |
| B | 5.13 | 5.50 |
| C | 0.88 | 1.28 |
| D | 5.90 | 6.22 |
| E | 0.68 | 1.10 |
| F | 0.68 | 0.91 |
| G | 2.29REF | |
| H | 2.90REF | |
| I | 0.85 | 1.17 |
| J | 0.51REF | |
| K | 2.10 | 2.50 |
| L | 0.40 | 1.00 |

Ordering Information

| Part | Package | Marking | Packing method |
|------------|---------|------------|----------------|
| WMO15N15T1 | TO-252 | WMO15N15T1 | Tape and Reel |

Marking Information



WMO15N15T1 = Device code

WWXX XXX= Date code

Contact Information

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